

What is claimed is:

205/80 1. A method of wiring formation comprising the steps of:

1 forming a feeder film partially on a substrate;

5 forming on the substrate a plating base film such that

the plating base film partially overlaps the feeder film;

forming a plated wiring on the plating base film; and

selectively removing at least a portion of the feeder

film that is exposed from the plated wiring.

216/80 10 2. A method of wiring formation according to Claim 1,

wherein the step of forming on the substrate a plating base

film is performed using a physical film making process.

15 3. A method of wiring formation according to Claim 1,
wherein the step of forming a plated wiring on the plating base

film is performed using an electrolytic plating process.

20 4. A method of wiring formation according to Claim 1,
wherein the step of selectively removing at least a portion of
the feeder film that is exposed from the plated wiring is
performed using a wet etching process.

25 5. A method of wiring formation according to Claim 1,
wherein a width of a portion of the plating base film that is
stacked on the feeder film is wider than the smallest wire
width of the feeder film.

30 6. A method of wiring formation according to Claim 1,
wherein the plating base film comprises at least one of an
adhesive layer and a diffusion preventive layer.

7. A method of wiring formation comprising the steps of:
forming a feeder film partially on a substrate;
5 forming on the substrate a resist pattern which has an
opening defining a wiring forming area, such that a portion of
the feeder film is exposed from the opening in the resist
pattern;

10 forming a plating base film at least on the substrate in
the opening;
forming a plated wiring on the plating base film in the
opening;

removing the resist pattern; and
selectively removing at least a portion of the feeder
film that is exposed from the plated wiring.

15 8. A method of wiring formation according to Claim 7,
wherein the step of forming on the substrate a plating base
film is performed using a physical film making process.

20 9. A method of wiring formation according to Claim 7,
wherein the step of forming a plated wiring on the plating base
film is performed using an electrolytic plating process.

25 10. A method of wiring formation according to Claim 7,
wherein the step of selectively removing at least a portion of
the feeder film that is exposed from the plated wiring is
performed using a wet etching process.

30 11. A method of wiring formation according to Claim 7,
wherein a width of a portion of the plating base film that is
stacked on the feeder film is wider than the smallest wire
width of the feeder film.

12. A method of wiring formation according to Claim 7,
wherein the plating base film comprises at least one of an
adhesive layer and a diffusion preventive layer.

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13. A method of manufacturing an electronic component
comprising the steps of:

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providing a substrate;
forming a feeder film partially on the substrate;
forming on the substrate a plating base film by using a
physical film making process such that the plating base film
partially overlaps the feeder film;

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forming a plated wiring on the plating base film using an
electrolytic plating process; and

selectively removing at least a portion of the feeder
film that is exposed from the plated wiring, using a wet
etching process.

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14. A method according to Claim 13, wherein a width of a
portion of the plating base film that is stacked on the feeder
film is wider than the smallest wire width of the feeder film.

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15. A method according to Claim 13, wherein a width of a
portion of the plating base film that is stacked on the feeder
film is wider than the smallest wire width of the feeder film.

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16. A method according to Claim 13, wherein the plating
base film comprises at least one of an adhesive layer and a
diffusion preventive layer.

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17. A method of manufacturing an electronic component comprising the steps of:

5 providing a substrate;

 forming a feeder film partially on a substrate;

 forming on the substrate a resist pattern which has an opening defining a wiring forming area, such that a portion of the feeder film is exposed from the opening in the resist pattern;

10 forming a plating base film at least on the substrate in the opening using a physical film making process;

 forming a plated wiring on the plating base film in the opening using an electrolytic plating process;

 removing the resist pattern; and

 selectively removing at least a portion of the feeder

15 film that is exposed from the plated wiring, using a wet etching.

18. A method according to Claim 17, wherein a width of a portion of the plating base film that is stacked on the feeder

20 film is wider than the smallest wire width of the feeder film.

19. A method according to Claim 17, wherein a width of a portion of the plating base film that is stacked on the feeder film is wider than the smallest wire width of the feeder film.

25 20. A method according to Claim 17, wherein the plating base film comprises at least one of an adhesive layer and a diffusion preventive layer.